

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Multiple sheets used when necessary)</i>	Application No.	10/692,243
	Filing Date	October 22, 2003
	First Named Inventor	Sherman
	Art Unit	1762
SHEET 1 OF 1		Attorney Docket No. ASMMC.9CP1DV1D

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
/D.T./		20a-ZC-1, MIYAMOTO et al., "High-Fluidity Deposition of SiN by Cryogenic Remote Plasma CVD," Research Center for Integrated Systems and Faculty of Engineering, Hiroshima University, 1 page	✓
/D.T./		20a-ZC-2, GOTOU et al., "Atomic-Layer Deposition of SiN by Remote Plasma CVD," Research Center for Integrated Systems, Hiroshima University, 2 pages	✓
/D.T./		20a-ZC-3, NAKAMURA et al., "Atomic-Layer Deposition of SiO ₂ by Remote Plasma CVD," Research Center for Integrated Systems, Hiroshima University, 1 page	✓

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Examiner Signature /David Turocy/	Date Considered 06/26/2007
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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